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STATEMENT BY APPLICANT Filing Date January 27, 2004							, 2004					
						First Nam	ed Inventor	Yos	Yoshihide SENZAKI			
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ³ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached. 1129872

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INF(DRN	MATION DISCLOSURE	Application Number	10/766,148 January 27, 2004 Yoshihide SENZAKI							
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Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.									
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